

# TABLE OF CONTENTS

Sl.No.	Title	Page No.
	List of Figures	ii
	List of Abbreviations	iii
1	Introduction	01
2	Radiation Effects	03
	2.1 Total Ionization Dose (TID)	03
	2.2 Single Event Effects (SEE)	04
3	Radiation Hardness in FPGA	05
	3.1 Scrubbing	05
	3.2 Triple Modular Redundancy	07
	3.3 SOI Radiation Hard Technology	08
4	SOS EEPROM-Based Configuration Cell	09
	4.1 Silicon On Sapphire EEPROM	09
	4.2 SOS EEPROM-Based Configuration Cell	11
	4.3 Current Sensing Mechanism	14
5	Auto-Scrubbing Behavior	17
	5.1 Soft Error Analysis	18
6	Conclusion	20
	References	22

## **LIST OF FIGURES**

Sl.No.	Title	Page No.
4.1	Basic Silicon-on-Sapphire EEPROM Cell	09
4.2	EEPROM charge storage characteristics.	10
4.3	EEPROM Cell with Schmitt Sense Amplifier	11
4.4	DC characteristics of the configuration cell	12
4.5	Sense Amplifier Static Current Behaviour	12
4.6	Layout of EEPROM cell with Schmitt sense amplifier	13
4.7	Current detection for odd and even memory bank.	14
4.8	Scrubbing state machine diagram.	15
5.1	Auto-scrubbing system configuration	17
5.2	MTBF Failure Mode	19

## **LIST OF ABBREVIATION**

SEU	Single Event Upset
TMR	Triple Modular Redundancy
SOI	Silicon On Insulator
SOS	Silicon On Sapphire
TID	Total Ionization Dose
SEE	Single Event Effects
MTBF	Mean Time Between Failure
FIT	Failure In Time
ICAP	Internal Configuration Access Port
LUT	Look Up Table
MTTR	Mean Time To Repair
MTBF	Mean Time Between Failure